

HIGH CURRENT APPLICATION.

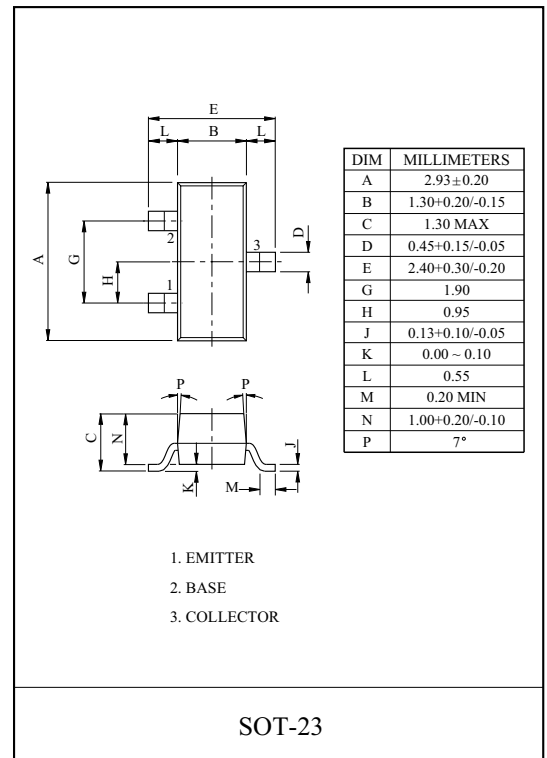
FEATURE

- Complementary to KTC8550S.

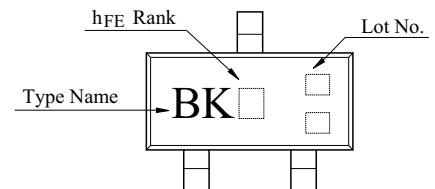
MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Emitter Current	I_E	-800	mA
Collector Power Dissipation	P_C^*	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 ~ 150	℃

* P_C : Package Mounted On 99.5% Alumina (10×8×0.6mm)



Marking



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=15V, I_E=0$	-	-	50	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=0.5mA, I_E=0$	35	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	30	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=1V, I_C=50mA$	100	-	300	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=350mA$	60	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=20mA$	-	-	0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=1V, I_C=500mA$	-	-	1.2	V
Transition Frequency	f_T	$V_{CE}=5V, I_C=10mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz, I_E=0$	-	13	-	pF

Note : $h_{FE(1)}$ Classification C : 100 ~ 200, D : 150 ~ 300

KTC8050S

